

# TRANSISTOR MODULE

# QCA200AA120

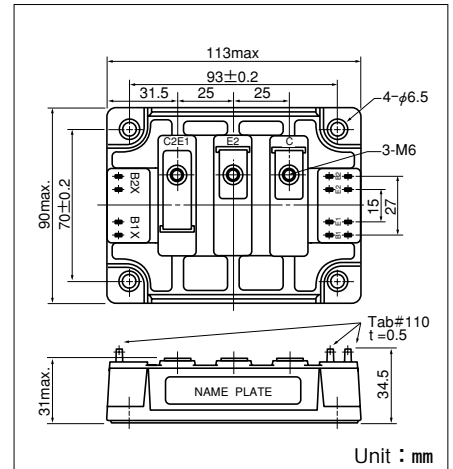
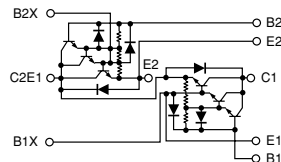
UL:E76102(M)

QCA200AA120 is a dual Darlington power transistor module with has series-connected high speed, high power Darlington transistors. Each transistor has a reverse paralleled fast recovery diode. The mounting base of the module is electrically isolated from semiconductor elements for simple heatsink construction.

- $I_C=200A$ ,  $V_{CEX}=1200V$
- Low saturation voltage for higher efficiency
- High DC current gain  $h_{FE}$
- Isolated monuting base

**(Applications)**

Motor Control (VVF), AC/DC Servo, UPS, Switching Power Supply, Ultrasonic Application



**Maximum Ratings**

( $T_j=25^{\circ}C$  unless otherwise specified)

| Symbol         | Item                                | Conditions                        | Ratings     |  | Unit            |
|----------------|-------------------------------------|-----------------------------------|-------------|--|-----------------|
|                |                                     |                                   | QCA200AA120 |  |                 |
| $V_{CBO}$      | Collector-Base Voltage              | Emitter open                      | 1200        |  | V               |
| $V_{CEX}$      | Collector-Emitter Voltage           | $V_{BE}=-2V$                      | 1200        |  | V               |
| $V_{CEX(SUS)}$ | Collector-Emitter Sustaning Voltage | $I_C=40A$ , $I_{B2}=-5A$          | 1200        |  | V               |
| $V_{EBO}$      | Emitterr-Base Voltage               | Collector open                    | 10          |  | V               |
| $I_C$          | Collector Current                   |                                   | 200         |  | A               |
| $-I_C$         | Reverse Collector Current           |                                   | 200         |  | A               |
| $I_B$          | Base Current                        |                                   | 10          |  | A               |
| $P_C$          | Collector-Emitter power dissipation | $T_C=25^{\circ}C$                 | 1560        |  | W               |
| $T_j$          | Junction Temperature                |                                   | -40 to 150  |  | $^{\circ}C$     |
| $T_{stg}$      | Storage Temperature                 |                                   | -40 to 125  |  | $^{\circ}C$     |
| $V_{iso}$      | Isolation Voltage(RMS)              | A.C. 1minute                      | 2500        |  | V               |
|                | Mounting Torque(M6)                 | Recommended Value 2.5-3.9 (25-40) | 4.7 (48)    |  | N·m<br>(kgf·cm) |
|                | Mass                                | Typical Value                     | 675         |  | g               |

**Electrical Characteristics**

| Symbol        | Item   | Conditions                  | Ratings  |       | Unit          |
|---------------|--|-----------------------------|--|-------|---------------|
|               |  |                             | Min.   | Max   |               |
| $I_{CBO}$     | Collector Cut-off Current                                      | $V_{CB}=1000V$ Emttter open |  | 4.00  | mA            |
| $I_{EBO}$     | Emitter Cut-off Current  | $V_{EB}=10V$ Collector open |  | 500   | mA            |
| $h_{FE}$      | D.C. Current Gain  | $I_C=200A$ , $V_{CE}=5V$    | 75   |       |               |
| $V_{CE(sat)}$ | Collector-Emitter Sturation Voltage                            | $I_C=200A$ , $I_B=4A$       |  | 3.0   | V             |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage                                | $I_C=200A$ , $I_B=4A$       |  | 3.5   | V             |
| $t_{on}$      | Switching Time   | On Time                     |  | 3.0   | $\mu s$       |
| $t_{stg}$     |  | Storage Time                | $V_{CC}=600V$ , $I_C=200A$<br>$I_{B1}=4A$ , $I_{B2}=-4A$ | 15.00 |               |
| $t_f$         |  | Fall Time                   |  | 3.0   |               |
| $V_{ECO}$     | Collector-Emitter Reverse Voltage (Diode forward voltage drop) | $-I_C=200A$                 |  | 1.8   | V             |
| $R_{th(j-c)}$ | Thermal Impedance (Junction to case)                           | Transistor part             |  | 0.08  | $^{\circ}C/W$ |
|               |  | Diode part                  |  | 0.35  |               |

